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(71) Applicant: **INTEL CORPORATION** [US/US]; 2200
Mission College Boulevard, Santa Clara, CA 95052 (US).

(72) Inventors: **SUNDARAM, Rajesh**; 9160 Madison Av-
enue, #43, Fair Oaks, CA 95628 (US). **JAVANIFARD,**
Jahanshir; 6236 Mahala Drive, Carmichael, CA 95608
(US).

(74) Agents: **MALLIE, Michael, J.** et al.; Blakely Sokoloff
Taylor & Zafman, 7th floor, 12400 Wilshire Boulevard, Los
Angeles, CA 90025 (US).

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(54) Title: VARIABLE VOLTAGE SOURCE FOR A FLASH MEMORY DEVICE

(57) Abstract: Variable voltage source (80) for a flash memory device. The variable voltage source (80) receives an input voltage (V) and provides an output voltage (Vout) for a read or write operations in the flash memory. The variable voltage source (80) further comprises a voltage-divider (170, 180, 190, 200) and a tap circuit (210) for selecting a tap point, according to the received data values in the control logic (230). The voltage selected from the tap point is compared with the voltage reference in the regulation circuit (220), which controls a transistor (150) for switching the output current flowing through the inductor (130).



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